

CLAIMS

1. (Amended) A semiconductor polishing composition comprising:

fumed silica as abrasive grains,

the semiconductor polishing composition being obtained by preparing a mixture of an acidic aqueous solution and fumed silica having wherein a bulk density of the fumed silica is 50 g/L or more and less than 100 g/L, and an alkali aqueous solution so that pH of the mixture is in a range of 1 to 3 and pH of the alkali aqueous solution is in a range of 12 to 14, and adding the mixture to the alkali aqueous solution continuously or intermittently.

2. The semiconductor polishing composition of claim 1, wherein a content of the fumed silica is in a range of 10% by weight to 30% by weight based on a total amount of the composition.

3. (Cancelled) ~~The semiconductor polishing composition of claim 1 or 2, wherein the semiconductor polishing composition is prepared by adding a mixture of an acidic aqueous solution and fumed silica to an alkali aqueous solution.~~

4. (Cancelled) ~~The semiconductor polishing composition of claim 3, wherein the pH of the alkali aqueous solution is in a range of 12 to 14.~~

5. (Cancelled) ~~The semiconductor polishing composition of any one of claims 1 to 4, wherein the pH of the mixture of fumed silica and water is in a range of 1 to 3.~~

6. (Amended) The semiconductor polishing composition of ~~any one of claims 31 to or 52~~, wherein the alkali aqueous solution contains one or two or more additives selected from a polishing accelerator, an oxidant, an organic acid, a complexing agent, a corrosion inhibitor and a surfactant.

7. (Amended) The semiconductor polishing composition of any one of claims 31 to 63, wherein alkali contained in the alkali aqueous solution is one or two or more hydroxides selected from ammonium hydroxide, alkali metal hydroxide, and alkaline earth metal hydroxide.